

PCN Number:	PCN# 20251014001.2			PCN Date:	October 14, 2025
Title:	Qualification of CDAT as an additional Assembly/Test site for select devices				
Customer Contact:	Change Management Team		Dept:	Quality Services	
Proposed 1st Ship Date:	April 12, 2026		Sample requests accepted until:	December 13, 2025*	
*Sample requests received after December 13, 2025 will not be supported.					
Change Type:					
<input checked="" type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material
<input checked="" type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input type="checkbox"/>	Wafer Fab Site
<input type="checkbox"/>	Mechanical Specification	<input checked="" type="checkbox"/>	Test Site	<input type="checkbox"/>	Wafer Fab Material
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input type="checkbox"/>	Wafer Fab Process
PCN Details					
Description of Change:					
Texas Instruments Incorporated is announcing the qualification of CDAT as an additional Assembly/Test site for the devices listed below. Construction differences are as follows:					
	HFTF	HNA	TFME	CDAT	
Mount Compound	4207123	SID#A-09	SID#A-09 SID# A-03	4207123 4226215	
Bond wire diam/type	0.8mil Cu	1.0mil Au	1.0mil Au	0.8mil Cu	
Mold Compound	SID#R-27	SID#450179	SID# R-07	4222198	
Lead finish	NiPdAu	NiPdAu	NiPdAu	Matte Sn	
Wafer thickness	6.0mil	7.5mil	7.5mil	6.0mil	
<p>Upon expiry of this PCN, TI will combine lead finish solutions in a single standard part number. For example, a customer order for 7500 units of a specific TI part number with 2500 units SPQ (Standard Pack Quantity per reel) may be fulfilled in the following ways:</p> <ul style="list-style-type: none"> • 3 reels of NiPdAu finish • 3 reels of Matte Sn finish • 2 reels of Matte Sn and 1 reel of NiPdAu finish • 2 reels of NiPdAu and 1 reel of Matte Sn finish <p>Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ</p> <p>Qual details are provided in the Qual Data Section.</p>					
Reason for Change:					
Supply continuity					
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):					
None					
Impact on Environmental Ratings					
Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.					
RoHS		REACH		Green Status	
<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change	
				IEC 62474	
				<input checked="" type="checkbox"/> No Change	

Changes to product identification resulting from this PCN:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
HFTF	HFT	CHN	Hefei
HNA	HNT	THA	Ayutthaya
TFME	NFM	CHN	Economic Development Zone
CDAT	CDA	CHN	Chengdu

Sample product shipping label (not actual product label)



Product Affected:

INA186A1QDCKRQ1*	INA186A3QDCKRQ1*	TLV70030QDCKRQ1
INA186A2QDCKRQ1*	SN74LV1T34QDCKRQ1	TS5A3166QDCKRQ1

* G4 part numbers are available and will remain on NiPdAu flows. This PCN does not apply to existing G4 materials. Please visit TI's [labeling and symbolization](#) page for more information on material designators

Automotive Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 06-December-2024

Product Attributes

Attributes	Qual Device: INA210BQDCKRTL	QBS Process Reference: INA215AQDCKRQ1	QBS Package Reference: TPS3840PH30DBVRQ1	QBS Package Reference: LM74703QDDFRQ1	QBS Package Reference: TXS0101QDCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Power Management	Power Management	Logic
Wafer Fab Supplier	AIZU	AIZU	RFAB	RFAB	RFAB
Assembly Site	CDAT	TFME	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT	SOT	SOT
Package Designator	DCK	DCK	DBV	DDF	DCK
Pin Count	6	6	5	8	6

QBS: Qual By Similarity, also known as Generic Data

Qual Device INA210BQDCKRTL is qualified at MSL1 260C

Note 1: Qual device and affected devices in PCN have justification to use Package QBS references for HAST, AC/UHAST and TC-BP based on AEC-100J A1.3 assembly site and package attributes were qualified.

Note 2: Qual device and affected devices in PCN have justification to use Process QBS references for HTOL and ELFR based on AEC-100J A1.2 silicon wafer fab and process attributes were qualified. Group B tests purpose is for silicon defects, they do not get influenced by assembly site or BOM differences.

Note 3: Qual device and affected devices in PCN have justification to use SD QBS based on AEC-100J A1.3 leadframe attributes are qualified.

Note 4: One lot is allowed per AEC-Q100J A1.5.1 Multiple Sites - When the specific product or process attribute to be qualified or requalified will affect more than one wafer fab site or assembly site, a minimum of one lot of testing per affected site is required.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: INA210BQDCKRTL	QBS Process Reference: INA215AQDCKRQ1	QBS Package Reference: TPS3840PH30DBVRQ1	QBS Package Reference: LM74703QDDFRQ1	QBS Package Reference: TXS01010DCKRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	1/Pass Note 4	-	3/Pass	3/Pass	3/Pass
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0 Note 4	-	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0 Note 4	-	3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	Note 1	-	1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0 Note 4	-	3/135/0	1/45/0	3/135/0
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	Note 2	3/231/0	3/231/0	-	1/77/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	Note 2	-	-	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	Note 2	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0 Note 4	-	3/30/0	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Tddb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0 Note 4	-	-	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0 Note 4	-	-	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0 Note 4	-	-	-	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2405-062

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at CDAT

Approve Date 06-December-2024

Attributes	Q006 Reference: TPS3840PH30DBVRQ1	Q006 Reference: LM74703QDDFRQ1	Q006 Reference: TXS0101QDCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT
Package Designator	DBV	DDF	DCK
Pin Count	5	8	6

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Q006 Reference: TPS3840PH30DBVRQ1	Q006 Reference: LM74703QDDFRQ1	Q006 Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/Pass	3/Pass	3/Pass
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	Note 1	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	Note 1	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0	Note 1	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	Note 1	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	Note 1	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	3/66/0	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	3/3/0	3/3/0
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	3/210/0	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0	3/3/0

TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	1/45/0 Note 1	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	1/1/0 Note 1	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0	1/44/0 Note 1	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	1/1/0 Note 1	3/3/0
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0

This report represents AEC-Q006 7.1 Family Data Usage using technology driver and lead products that are most representative of the technology family.

Note 1: LM74703QDDFRQ1 HAST and HTSL QBS'd to TPS3840PH30DBVRQ1 that has same Assembly site, package, bond pad metal, wire and mold attributes.

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2405-062

Automotive New Product Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 02-July-2025

Product Attributes

Attributes	Qual Device: CAHC1G125QDCKRQ1	QBS Process Reference: SN74HCS74QFWRQ1	QBS Package Reference: TL331QDBVRQ1	QBS Package, Product Reference: CAHCT1G125QDBVRQ1	QBS Package Reference: TXS0101QDCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain,Logic	Logic	Signal Chain	Logic	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB
Assembly Site	CDAT	MLA	CDAT	CDAT	CDAT
Package Group	SOT	TSSOP	SOT	SOT	SOT
Package Designator	DCK	PW	DBV	DBV	DCK
Pin Count	5	14	5	5	6

QBS: Qual By Similarity, also known as Generic Data

Qual Device CAHC1G125QDCKRQ1 is qualified at MSL1 260C

Per AEC-Q100J A1.3: The PCN devices are categorized as a qualification family and use generic data that has been qualified for the critical attributes in Die sizes, Package Type, Assembly Process and Site

Note 1: Qual Device and affected devices in PCN have justification to use Package and Process QBS references for Group A, Group B and Group C tests based on AEC-100J Appendix 1 A1.2 and A1.3. The fab, assembly site and package attributes were qualified.

Note 2: Other devices have passed HBM/CDM/LU with the final wafer/backgrind thickness. TI will not re-run

HBM/CDM/LU for this change since backgrind removes bulk silicon and does not affect the active area of die.

HBM/CDM/LU purpose is to test the active area of die, die circuit design and/or wafer fab defects that would result damage to dielectrics, junctions, metal.

Note 3: ED cannot use Generic data per AEC-Q100J but there is representation of passing Electrical Distributions in QBS Package devices with the same assembly site and package attributes.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CAHC1G125QDCKRQ1	QBS Process Reference: SN74HCS74QFWRQ1	QBS Package Reference: TL331QDBVRQ1	QBS Package, Product Reference: CAHCT1G125QDBVRQ1	QBS Package Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	Note 1	-	3/Pass	3/Pass	3/Pass
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	1/77/0	3/231/0
AC/HAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	1/77/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	Note 1	-	3/231/0	1/77/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	Note 1	-	1/6/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	Note 1	-	-	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	Note 1	-	1/45/0	1/45/0	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	Note 1	3/231/0	-	-	3/231/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	Note 1	-	1/77/0	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	Note 1	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0	3/90/0

SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	Note 1	1/15/0	1/15/0	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	Note 1	1/15/0	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0	1/10/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Tddb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Note 2	-	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	Note 2	-	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	Note 2	-	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	Note 3	-	1/30/0	1/30/0	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2502-024

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at CDAT

Approve Date 02-July-2025

Attributes	QBS Package Reference:	
	<u>TXS0101QDCKRQ1</u>	
Automotive Grade Level	Grade 1	
Operating Temp Range (C)	-40 to 125	
Product Function	Logic	
Wafer Fab Supplier	RFAB	
Assembly Site	CDAT	
Package Group	SOT	
Package Designator	DCK	
Pin Count	6	

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	QBS Reference: <u>TXS0101QDCKRQ1</u>
Test Group A - Accelerated Environment Stress Tests								
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/Pass
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0

TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0
Test Group C - Package Assembly Integrity Tests								
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0

This report represents AEC-Q006 7.1 Family Data Usage using technology driver and lead products that are most representative of the technology family.

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

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TI Qualification ID: R-CHG-2502-024

ZVEI IDs: SEM-PW-03, SEM-PA-05, SEM-PA-07, SEM-PA-08, SEM-PA-11, SEM-PA-18, SEM-TF-01

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Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

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